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## **BC182B**

- NPN General Purpose Amplifier

  This device is designed for general purpose amplifier application at collector currents to 100mA.
- Sourced from process 10.



1. Collector 2. Base 3. Emitter

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current - Continuous	100	mA
T <sub>J,</sub> T <sub>STG</sub>	Storage Junction Temperature Range	- 55 ~ 150	°C

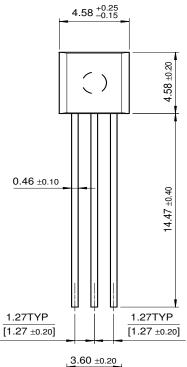
### **Electrical Characteristics** $T_C=25$ °C unless otherwise noted

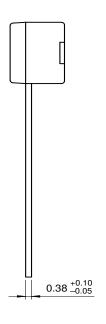
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Chara	cteristics		-			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 2mA, I_B = 0$	50			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 50V, V_{BE} = 0$			15	nA
I <sub>EBO</sub>	Emitter-Base Leakage Current	$V_{EB} = 4V, I_{E} = 0$			15	nA
On Chara	cteristics		-			
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 10\mu A$ $V_{CE} = 5V, I_{C} = 100m A$	40 80			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$ $I_C = 100 \text{mA}, I_B = 5 \text{mA}$			0.25 0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA			1.2	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = 5V$ , $I_C = 2mA$	0.55		0.7	V
Dynamic (	Characteristics			•	•	•
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA, f = 100MHz 150			MHz	
C <sub>ob</sub>	Output Capacitance	V <sub>CE</sub> = 10V, I <sub>C</sub> = 0, f = 1MHz			5	pF
h <sub>fe</sub>	Small Signal Current Gain	$V_{CE} = 5V$ , $I_C = 2mA$ , $f = 1KHz$	240		500	
NF	Noise Figure	$V_{CE}$ = 5V, $I_{C}$ = 0.2mA $R_{S}$ = 2K $\Omega$ , f = 1KHz, BW = 200Hz			10	dB

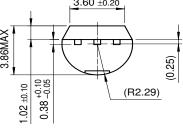
Thermal Characteristics T <sub>A</sub> =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation @T <sub>A</sub> =25°C Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W

# **Package Dimensions**

TO-92







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